Data Sheet No. PD-1.017B

## INTERNATIONAL RECTIFIER

## SERIES DP

Microelectronic Power IC Relay

> 1 Amp 20-280V AC

# ChipSwitch DIP Relay

#### GENERAL DESCRIPTION

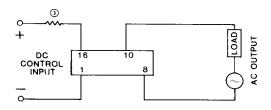
The ChipSwitch DIP uses the exclusive International Rectifier S'X power integrated circuit technology to form a fully functioning solid-state relay. The S'X technology combines MOS and bipolar processes, derived from IRs HEXFET power MOSFET designs, to eliminate the need for both discrete components and hybrid circuits. The basic ChipSwitch DIP consists simply of two identical power integrated circuits connected in inverse parallel (analogous to back-to-back SCRs) for AC control plus an isolated light emitting diode (LED) for actuation. Voltage controlled models with an internal resistor to limit the control current are also available

Extreme reliability is achieved by the reduction of component count from approximately 20 discrete components in a conventional SSR to 3 basic components in the ChipSwitch. The power integrated circuits are fabricated in IR's advanced MOSFET fabrication plant which achieves standards of cleanliness, precision, and consistency unprecedented in the manufacture of power semiconductors

The ChipSwitch is a normally open SSR of 1.0 ampere rating with precise zero voltage turn-on and zero current turn-off. EMI emission conforms to the most severe FCC and VDE

The devices are ideally suited for interfacing microprocessors to AC loads such as small motors, lamps, solenoids, valves, and high power motor starters. The economy of the ChipSwitch allows the in-house manufacturer to replace assemblies of triacs, triac drivers and associated components with a highly reliable, miniature, standard SSR

### WIRING DIAGRAM



- S³X Power IC Chips 30 Amps Surge ■
- 4000V RMS isolation Zero Voltage Turn-On ■ EMI Meets FCC/VDE Limits ■
- Operates Without Snubber m
  - 600V/µsec dv/dt 10 Microamps Leakage ■
  - TO-116 Pinout ■
- 94 UL Recognized File E50015



#### Part Identification

Part No.	Transient Overvoltage (Vpk)	Operating Voltage (VRMS)	DC Input Turn-On		
DP1110 DP1210 DP1610	300	20-140	5 mA 10 mA 3.5 V		
DP2110 DP2210 DP2610	450	20-280	5 mA 10 mA 3.5 V		
DP6110 DP6210 DP6610	600	20-280	5 mA 10 mA 3 5 V		

# ChipSwitch DIP



GENERAL CHARAC	TERISTICS ELE	CTRICAL SPECIFICATIONS (-30°C ≤ T <sub>A</sub> ≤ 85°C unles	ss otherwise specified
Dielectric Strength — Input/Output		4000	V (RMS)
Insulation Resistance @ 500VDC — Input/Output		1012	Ohms
Tracking Resistance (VDE Test)		KB 100/A	_
Max Capacitance — Input/Output		2.0	pF
Ambient Temperature Range	Operating	- 30 to 85	°C
	Storage	- 40 to 100	°C
Lead Temperature (1.6 mm below seating plane) for 10 sec		sec. 260	°C

INPUT CHARACTERISTICS	DP1110	DP1210	DP1610	DP2110	DP2210	DP2610	DP6110	DP6210	DP6610	Units
Control Current Range ② (see Fig. 3)	5-25	10-25	N/A	5-25	10-25	N/A	5-25	10-25	N/A	mA (DC)
Control Voltage Range (see Fig. 4)	N.	N/A 35-7 N/A 35-7 N/A		3 5-7	V (DC)					
Max Reverse Voltage		70						V (DC)		
Max Turn-On Voltage	N.	/A	3.5	N	/A	35	N	/A	3.5	V (DC)
Min Turn-Off Voltage	N.	/A	08	N	/A	0.8	N	/A	08	V (DC)
Min Input Impedance	N.	/A	270	N	/A	270	N	/A	270	Ohms
Max Turn-On Current	5.0	10	N/A	50	10	N/A	50	10	N/A	mA (DC)
Min Turn-Off Current	0	.5	N/A	0	.5	N/A	0	5	N/A	mA (DC)
Max Turn-On Time (60 Hz)		8.3						mSec		
Max Turn-Off Time (60 Hz)		83						mSec		

OUTPUT CHARACTERISTICS							
Operating Voltage Range (47-440 Hz)	20-140	20-280	20-280	V (RMS)			
Transient Overvoltage (Non-Repetitive)	300	450	600	V (peak)			
Mın Off-State dv/dt (static) ① @ Max Rated Voltage (25°C)		V/μs					
Max Load Current (see Fig. 1)		A (RMS)					
Min Load Current		mA (RMS)					
Power Factor Range							
Max Surge Current (Non-Rep ) Single Cycle 20 ms (see Fig. 2)		A (peak)					
Max Over Current (Non-Rep.) 1 sec		A (peak)					
Max On-State Voltage Drop @ Rated Current		V (peak)					
Max PT for Fusing (.01 sec)		A <sup>2</sup> sec					
Max Zero Voltage Turn-On		V (peak)					
Max Peak Repetitive Turn-On Voltage @ 20mA Input		V (peak)					
Max Off-State Leakage Current③  @ Max. Operating Voltage, 25°C		10		μA (RMS)			

**GENERAL NOTES** 

Data and specifications subject to change without notice

② Current limiting resistor required for current controlled models.

<sup>Off-state dv/dt test method per EIA/NARM standard RS-443 with V<sub>D</sub> equal to the instantaneous peak of the maximum operating voltage</sup> 

<sup>3</sup> LED input current of zero MA

## ChipSwitch DIP

### PERFORMANCE CHARACTERISTICS CURVES

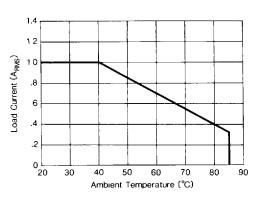


Figure 1. Derating Curve

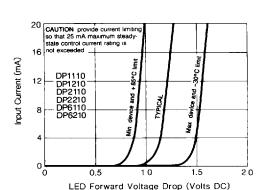


Figure 3. Input Characteristics (Current Controlled)

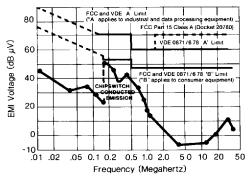


Figure 5. Conducted Electromagnetic Interference.
(Measured With DP1XXX and DP2XXX Models)

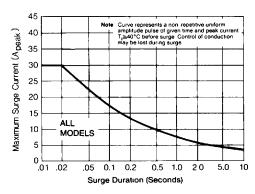


Figure 2. Max. Allowable Surge

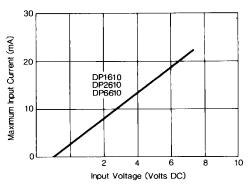


Figure 4. Input Characteristics (Voltage Controlled)

